IN THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A pattern forming method comprising:

forming a liquid-repellent thin film on an insulating surface, the liquid-repellent thin film being repellent to a liquid composition;

moving a first nozzle and a second nozzle, which are integrated, to a selected portion of the liquid-repellent thin film;

irradiating [[a]] the selected portion of the liquid-repellent thin film with plasma from [[a]] the first nozzle so that the selected portion has a liquid affinity to the liquid composition; and

forming a pattern by applying a drop of the liquid composition to the selected portion from [[a]] the second nozzle surface.

2. (Currently Amended) A pattern forming method comprising:

forming a thin film having an affinity for a liquid composition on an insulating surface;

moving a first nozzle and a second nozzle, which are integrated, to a selected portion of the thin film;

selectively forming a groove or a hole in a surface of ~~the thin film~~ the selected portion by selectively treating the ~~thin film~~ selected portion with a plasma from [[a]] the first nozzle; and

forming a pattern by applying a drop of the liquid composition to the groove or the hole in the ~~thin film~~ selected portion from [[a]] the second nozzle.

3. (Previously Presented) A pattern forming method according to claim 1, wherein the liquid composition comprises at least one selected from the group consisting of a conductive material, a resist material, a polymer material and a light emitting material.

4. (Original) A pattern forming method according to claim 1, wherein the liquid-repellent thin film is selected from the group consisting of a semiconductor film, a conductive film and a polymer film.

5. (Previously Presented) A pattern forming method according to claim 2, wherein the thin film having affinity for the liquid composition is selected from the group consisting of a silicon oxide film, silicon nitride film, a silicon oxynitride film and a metal oxide film.

6. (Previously Presented) A pattern forming method according to claim 1, wherein the irradiation with the plasma is performed at a pressure in a range of 1.3×10^1 to 1.31×10^5 Pa.

7. (Currently Amended) A pattern forming method according to claim 1, wherein a contact angle θ of ~~the surface having affinity~~ the selected portion of the liquid-repellent thin film, which is irradiated with plasma, for the liquid composition is $0° \leq \theta < 10°$, and a contact angle θ of ~~the liquid-repellent surface~~ the liquid-repellent thin film for the liquid composition is $10° \leq \theta < 180°$.

8-15. (Canceled)

16. (Previously Presented) A pattern forming method according to claim 2, wherein the liquid composition comprises at least one selected from the group consisting of a conductive material, a resist material, a polymer material and a light emitting material.

17. (Previously Presented) A pattern forming method according to claim 2, wherein the treatment of the thin film with the plasma is performed at a pressure in a range of 1.3×10^1 to 1.31×10^5 Pa.

18. (Currently Amended) A pattern forming method according to claim 2, wherein a contact angle θ of the ~~surface having affinity~~ thin film for the liquid composition is $0° \leq \theta < 10°$.

19-22 (Canceled).

23. (Currently Amended) A pattern forming method comprising:

moving a first nozzle and a second nozzle, which are integrated, to a selected portion of a surface;

irradiating [[a]] the selected portion of [[a]] the surface with plasma of a gas from [[a]] the first nozzle so that the selected portion has a liquid affinity to a liquid composition comprising a conductive material; and

forming a conductive pattern by applying a drop of the liquid composition to the selected portion from [[a]] the second nozzle;

forming a mask pattern of a resist over the conductive pattern; and

forming a wiring by etching the conductive pattern using the mask pattern.

24. (Previously Presented) A pattern forming method according to claim 23 wherein the gas is selected from the group consisting of He, Ne, Ar, Kr, Xe, oxygen, nitrogen and a combination thereof.

25. (Previously presented) A pattern forming method according to claim 23 wherein the mask pattern is formed by selectively applying the resist to the conductive pattern through a nozzle.

26. (Currently Amended) A pattern forming method comprising:

moving a first nozzle and a second nozzle, which are integrated, to a selected portion of a surface;

forming a groove in [[a]] ~~surface~~ the selected portion of the surface by selectively treating the surface with plasma of a gas from [[a]] the first nozzle; and

forming a conductive pattern by applying a liquid drop composition comprising a conductive material to the groove from [[a]] the second nozzle;

forming a mask pattern of a resist over the conductive pattern; and

forming a wiring by etching the conductive pattern using the mask pattern.

27. (Previously Presented) A pattern forming method according to claim 26 wherein the gas is selected from hydrogen, CF_4, NF_3, SF_6, oxygen and a combination thereof.

28. (Previously Presented) A pattern forming method according to claim 26 wherein the mask pattern is formed by selectively applying the resist to the conductive pattern through a nozzle.

29. (Previously Presented) A pattern forming method according to claim 1, wherein the application of the liquid composition is performed at a pressure in a range of 1.3×10^{1} to 1.31×10^{5} Pa.

30. (Previously Presented) A pattern forming method according to claim 2, wherein the application of the liquid composition is performed at a pressure in a range of 1.3×10^{1} to 1.31×10^{5} Pa.